

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	9532	capacitor and transistor and memory and trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/26 18:33
L2	1641	1 and (high near2 constant)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/26 18:34
L3	1569	2 and ((high near2 dielectric near2 constant) or (high near k))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/26 18:34
L4	169	3 and ((hafnium adj oxide) or (lanthanum adj oxide) or (yttrium adj oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/26 18:35
L5	35	4 and (trench\$2 near5 capacitor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/26 18:35
L6	45	3 and ((hafnium adj oxide).clm. or (lanthanum adj oxide).clm. or (yttrium adj oxide).clm.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/26 18:36
L7	45	6 and trench\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/26 18:36
L8	18	6 and (trench\$2 near6 capacitor\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/26 18:36